The First European GaN Workshop (EGW-1)

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The past several years have seen GaN move from a research topic to a major segment of the worldwide compound semiconductor market. The booming interest in GaN has been driven by the development of Candela class blue, blue-green, and now green commercial LEDs which have rapidly replaced entrenched SiC- and GaP-based LED technologies, and promise to dramatically grow the whole LED market enabling bright, full colour, large area LED displays, and LED-based traffic signals.

The GaN fever grew white hot with the December announcement by Nichia Chemical of a GaN-based diode laser, which is the shortest wavelength semiconductor laser ever made, and is expected to profoundly impact optical storage applications.

EGW-1 will be the first major meeting on European soil dedicated to GaN and its alloys with InN and AlN. The organizers take the concept of a workshop very seriously and intend to promote an open, friendly atmosphere conducive to the free exchange of information and the formation of future collaborations. This is important because European GaN researchers have recently converged from many diverse fields and have not yet had the opportunity to meet their colleagues in a European setting.

These goals influenced the selection of Rigi, a mountaintop village in the Swiss Alps near Luzern, where the attendees will share a single hotel and all meals during the conference. Participants will be limited to 100 persons, but an invitation is guaranteed to at least one representative of any European institution which wishes to attend. A single session is planned throughout, composed of papers limited to 5 - 10 min each, with each set immediately followed by an open panel discussion. This insures that each participant can hear and comment on every submission.

EGW-1 is being organized in cooperation with the Materials Research Society Internet Journal of Nitride Semiconductor Research (http://nsr.mij.mrs.org), a new electronic journal specializing in the GaN field, which will publish the workshop proceedings at a significant discount to normal journal rates. The MIJ-NSR will be on site in Rigi to provide assistance and instruction to attendees interested in rapid, paperless dissemination of their results. This collaboration has also enabled EGW-1 to accept electronic submission of camera ready abstracts, as both a convenience, and a first step to submitting the full work to MIJ-NSR. EGW-1 is also cooperating with the European MRS, which is hosting a special session on GaN immediately following the workshop.

The organizers have invited two prominent GaN researchers from outside of Europe to present their results. Prof. Robert Davis of North Carolina State University will describe his group's leading work on AlGaN alloys, especially in increasing the doping levels to reduce device operating voltages. Dr. Vladimir Dmitriev of Cree Research will present his company's commercial GaN/SiC LED technology.

The meeting runs two full days from Sunday evening until Tuesday afternoon. Guests will be greeted at an opening reception which will include an open bar and traditional Swiss music. A vendor exhibition will run concurrently to the technical program on both Monday and Tuesday. After a full day of papers on Monday, the participants will reconvene after dinner for a GaN Rump Session which is anticipated to be lively, not the least for the free drinks which will be available.

EGW-1 closes on Tuesday afternoon, early enough to permit participants to meet their connecting trains.

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